



Title: High-Electron Mobility Transistor With  
Zinc Oxide  
Inventors: Nause, et al.  
Atty Dkt. No. 046361/265061

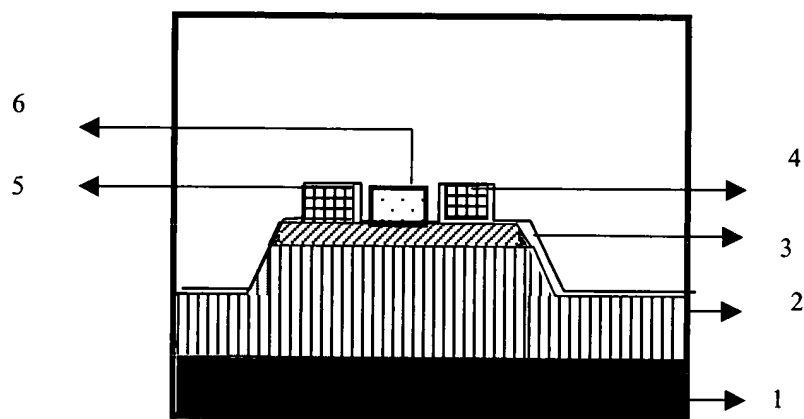


Figure 1: Layer Structure of the HEMT

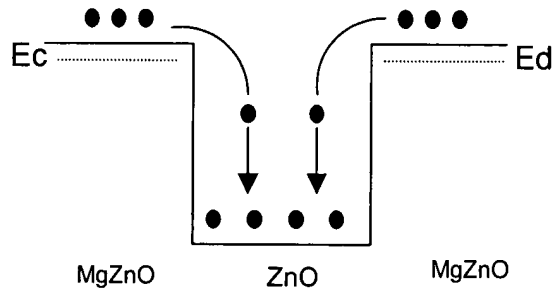


Figure 2A: Band diagram showing the band bending

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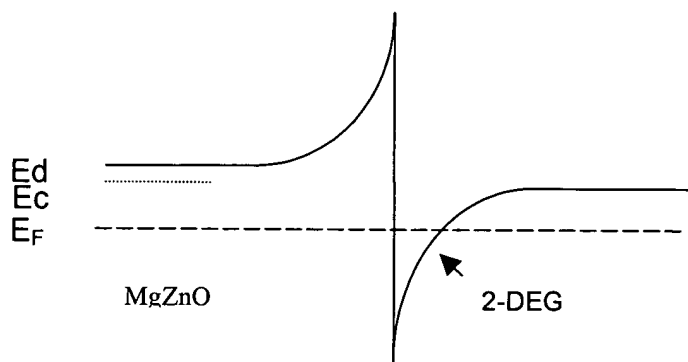


Figure 2B: Formation of 2DEG electron gas